PATENT COOPERATION TREATY

PCT

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY (Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or agent's file reference T 46451WO/NZ/hs		FOR FURTHER ACTION	See Form PCT/IPEA/416			
International application No.		International filing date (day/n	month/year) Priority date (day/month/year)			
PCT/DE20	004/001376	30.06.2004	03.07.2003			
•	nt Classification (IPC) or nati	onal classification and IPC				
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Applicant						
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<u> </u>						
 This report is the international preliminary examination report, established by this International Preliminary Examining Authority under Article 35 and transmitted to the applicant according to Article 36. 						
2. This RE	2. This REPORT consists of a total of sheets, including this cover sheet.					
3. This report is also accompanied by ANNEXES, comprising:						
a. 🔀	a. (sent to the applicant and to the International Bureau) a total of sheets, as follows:					
	sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or					
sheets containing rectifications authorized by this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions).						
	sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the Supplemental					
<u> </u>	Box.					
b. <u></u>	(sent to the International	Bureau only) a total of (indicate	e type and number of electronic carrier(s))			
			, containing a sequence listing and/or tables			
{	related thereto, in computer Section 802 of the Adminis		ated in the Supplemental Box Relating to Sequence Listing (see			
4 771			OPRECIED			
4. This rep	oort contains indications relati	ing to the following items:	ORREULL			
Box No. I Basis of the report Box No. II Priority Box No. II Priority						
Box No. II Priority			MFKOIOI			
	Box No. III Non-establi	ishment of opinion with regard	to novelty, inventive step and industrial applicability			
	Box No. IV Lack of uni	ity of invention				
	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability;					
	citations and explanations supporting such statement					
	Box No. VI Certain documents cited					
	Box No. VII Certain def	ects in the international applica	ation			
	Box No. VIII Certain obs	servations on the international a	pplication			
Date of submission	on of the demand	Date of	f completion of this report			
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Name and mailin	g address of the IPEA/EP	Author	rized officer			
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Translation

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Box No.	o. I Basis of the report						
	Vith regard to the language, this report is based on the internation dicated under this item.	al application in the language in which it was filed,	unless otherwise				
	This report is based on translations from the original language into the following language which is the language of a translation furnished for the purposes of:						
	international search (Rule 12.3 and 23.1(b)) publication of the international application (Rule 12.4)						
	international preliminary examination (Rule 55.2 and/or 55.3)						
re	Vith regard to the elements of the international application, this receiving Office in response to an invitation under Article 14 are his report): the international application as originally filed/furnished the description:	referred to in this report as "originally filed" an	d are not annexed to				
	pages <u>1-7</u>						
	pages*	received by this Authority on					
	pages*	received by this Authority on					
	the claims:						
	nos. 2-8	as origi	nally filed/furnished				
	nos.*	as amended (together with any stateme	ent) under Article 19				
İ	nos.* 1	received by this Authority on of 16.08.2005	with letter				
		received by this Authority on					
l Þ	the drawings:						
ļ <u> </u>	sheets 1/2-2/2	as origi	inally filed/furnished				
	sheets*		•				
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	a sequence listing and/or any related table(s) - see Supplem	emai Box Relating to Sequence Listing.					
3.	The amendments have resulted in the cancellation of:						
	the description, pages						
	the claims, nos.						
	the drawings, sheets/figs						
	the sequence listing (specify):		 				
	any table(s) related to sequence listing (specify):						
4.	This report has been established as if (some of) the amend they have been considered to go beyond the disclosure as fi	lments annexed to this report and listed below had led, as indicated in the Supplemental Box (Rule 70	not been made, since .2(c)).				
	the description, pages						
	the claims, nos.						
	the drawings, sheets/figs		<u> </u>				
	the sequence listing (specify):						
	any table(s) related to sequence listing (specify):						
* h	If item 4 applies, some or all of those sheets may be marked "sup	erseded."					

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Box No. V Reasoned statement under Ar citations and explanations sup		article 35(2) with regard to novelty, inventive step or industrial applicability; upporting such statement			
1.	Statement				
	Novelty (N)	Claims	1-8	YES
			Claims		NO
	Inventive s	tep (IS)	Claims		YES
			Claims	1-8	NO NO
	Industrial a	applicability (IA)	Claims	1-8	YES
			Claims		NO

2. Citations and explanations (Rule 70.7)

1. Documents

The present report refers to the following documents:

D1: ULLMANN A ET AL: "HIGH PERFORMANCE ORGANIC FIELD-EFFECT TRANSISTORS AND INTEGRATED INVERTERS" MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS, MATERIALS RESEARCH SOCIETY, PITTSBURG, PA, US, Vol. 665, 20 April 2001 (2001-04-20), pages 265-270, XP008032774 ISSN: 0272-9172

D2: US 3 955 098 A (KAWAMOTO HIROSHI) 4 May 1976 (1976-05-04)

D3: PATENT ABSTRACTS OF JAPAN, Vol. 0030, No. 90 (E-127), 31 July 1979 (1979-07-31) &; JP 54 069392 A (NEC CORP), 4 June 1979 (1979-06-04)

2. Inventive step

Pursuant to the requirements of PCT Article 33(1), the subject matter of claims 1-8 is not inventive (PCT Article 33(3)).

2.1 Independent claim 1

D1 discloses (the references relate to said document):

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Box No. V

Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

An organic logic gate comprising at least one charging FET and one switching FET (figure 5), wherein the charging FET has a gate, a source and a drain electrode (figure 5).

The subject matter of claim 1 differs from D1 in that the gate electrode of the charging FET is not connected to a voltage source via a line. In conjunction with the description (page 2, paragraph 5), the problem of interest can be seen as that of designing a logic gate that switches more quickly. D3, on the other hand, describes the problem of accelerating the switching time of the inverter gate (see PAJ abstract). The gate electrode of the charging FET is designed as a "floating" gate electrode (see PAJ abstract and figures 2 and 3). This "floating" gate electrode is not connected to a voltage source via a line. Although D3 describes a gate based on standard Si technology, a person skilled in the art is aware that organic and inorganic semiconductors differ from one another only on account of their materials (just as inorganic semiconductors also differ amongst each other). In the realm both of inorganic and organic semiconductors, a person skilled in the art can choose from a large number of materials. Consequently, solutions to problems from inorganic circuit technology can likewise be applied to organic circuits, and where required, the materials can be adapted to the circuitspecific requirements.

A person skilled in the art would therefore apply the teaching of D3 to the device of D1 and arrive thereby at the subject matter of claim 1. He would do this without

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Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

being inventive.

In addition, attention is drawn to the fact that an inventive step is not involved either if D2 or D3 is used as the closest prior art. D2 and D3 differ from claim 1 in that they do not describe the use of organic but rather of inorganic materials. D3 shows in figures 2 and 3 an inverter with a floating gate electrode which also has a substrate connection. However, a person skilled in the art is aware that this substrate connection is only optional and does not influence the basic functionality of the inverter. The gate in D2 (figure 2A) does not have such a substrate connection.

The problem of interest arising therefrom is that of designing a logic gate from non-inorganic material.

However, a person skilled in the art is aware that inorganic and organic circuits differ from one another only in their materials and the associated different processing methods and electronic properties of the material. Where required, organic materials which correspond to the respective inorganic materials must be chosen. In this respect, a gate based on Si technology differs more from an As-based gate than from an organic gate since, in the latter case, a person skilled in the art has a number of materials available with which he can mimic the Si gate. The principle layout of logic gates can therefore be applied unchanged from inorganic to organic circuits.

A person skilled in the art would do that as a matter of routine and without thereby being inventive.

2.2 Dependent claims 2-8

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Box No. V

Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

Claims 2-7 describe the additional features that the gate electrode of the charging FET is coupled capacitively and/or resistively to the source or drain electrode. As is apparent from figure 1 of D1, the "standard" OFET design, characterised by the overlap of the electrodes, always gives rise to a capacitive coupling between the source/drain electrodes and the gate electrode. Furthermore, the resistance between these electrodes has a finite value, and therefore it is possible also in this case to speak of a resistive coupling between the electrodes. Claims 2-7 are therefore not novel. Claim 8 discloses a logic gate that does not have a through contact. This is a trivial option which arises from the use of a floating gate, which is one of the numerous options for using the charging FET as a resistor (see also D2 and D3). A person skilled in the art would therefore choose this feature without thereby being inventive.

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Box No. V	Certain documents cited			
1. Certa	in published documents (Rule 70.10)			
	Application No. Patent No.	Publication date (day/month/year)	Filing date (day/month/year)	Priority date (valid claim) (day/month/year)
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see 1	incernacional SealCii	reporc.		
2. Non-	written disclosures (Rule 70.9)	<u> </u>		
	Kind of non-written disclosure	Date of non-written di (day/month/yea	sclosure referri	nte of written disclosure ng to non-written disclosure (day/month/year)
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